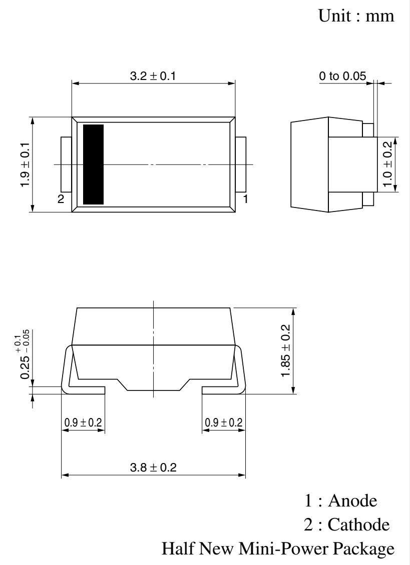
MA2H735

Silicon epitaxial planar type

For switching circuits



Marking Symbol: A

■ Features

- Small and thin Half New Mini-power package
- Allowing to rectify under ($I_{F(AV)} = 1$ A) condition
- Low V_F (forward voltage) type: $V_F > 0.5$ V (at $I_F = 1$ A)

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	30	V
Repetitive peak reverse voltage	V_{RRM}	30	V
Average forward current	$I_{F(AV)}$	1	A
Non-repetitive peak forward surge current*	I_{FSM}	30	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	−40 to +125	°C

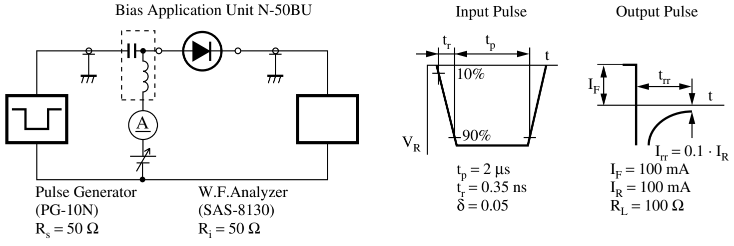
Note) * : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

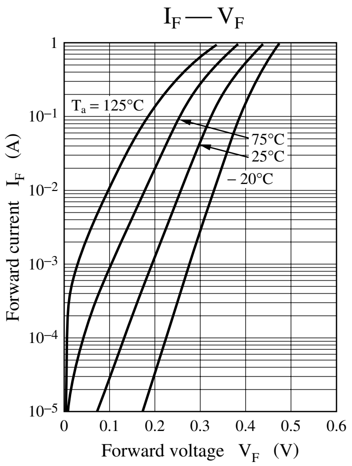
■ Electrical Characteristics $T_a = 25°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 30$ V			1	mA
Forward voltage (DC)	V_F	$I_F = 1$ A			0.50	V
Terminal capacitance	C_t	$V_R = 10$ V, f = 1 MHz		50		pF
Reverse recovery time*	t_{rr}	$I_F = I_R = 100$ mA $I_{rr} = 0.1 \cdot I_R$, $R_L = 100\ \Omega$			30	ns

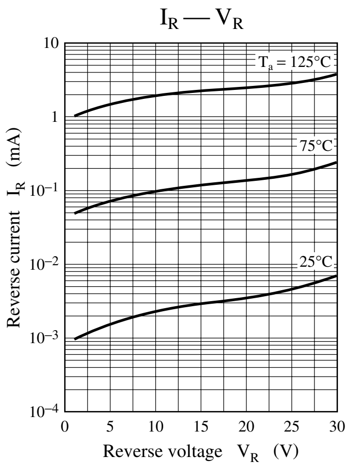
Note) 1. Rated input/output frequency: 20 MHz

2. * : t_{rr} measuring instrument

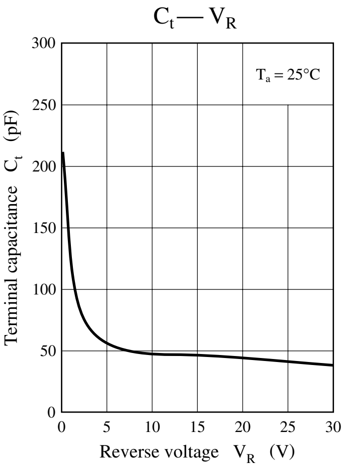




I_F — V_F



I_R — V_R



C_t — V_R